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Moor than Moore, IoT, and Manufacturing Challenges

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Foreword

On behalf of VDE/VDI-GMM, the sponsors, and the organizing committee, we would like to welcome you to the proceedings from the 32nd European Mask and Lithography Conference, EMLC2016, at the Hilton Hotel in Dresden, Germany.

The conference has annually brought together scientists, researchers, engineers, and technologists from research institutes and companies from around the world to present innovations at the forefront of mask and wafer lithography. The two-day conference was dedicated to the science, technology, engineering and application of mask and lithography technologies and associated processes—giving an overview of the present status of mask and lithography technologies, while also providing future strategies where mask producers and users have the opportunity of becoming acquainted with new developments and results. This year’s sessions included: Mask Patterning, Metrology and Process, Wafer Lithography, EUV, Modelling and Computational Process Correction, Photonics, More than Moore, IoT and Manufacturing Challenges, Using the Data, Novel Approaches, and Nano-Imprint Lithography.

Rutger Wijburg from Globalfoundries (Dresden) was the welcome speaker and first keynote speaker. He presented, “The Semiconductor Industry in Transition: A European Perspective.”

The second keynote speaker was Naoya Hayashi from Dai Nippon Printing, Japan. His talk was titled, “Challenges and Prospects of Next Generation Masks” The status of the worldwide mask technologies.”

The third keynote speaker was You Cao from ASML Brion Inc. (USA) who presented “Computational Lithography and Applications in Process Window Enhancement and Control.”

On Monday morning, the Best Poster from BACUS 2015 was presented, followed by the Best Paper from PMJ 2016.

Technical Exhibition

Parallel to the conference presentations, a technical exhibition took place on Tuesday and Wednesday where companies (mask suppliers, material suppliers and equipment suppliers) presented their companies and products. To foster the exchange between the conference attendees and the exhibitors, the exhibition area was also the place for all coffee and lunch breaks.
We hope that you enjoyed the technical sessions of the EMLC2016 as well as the technical exhibition, but also allowed yourself to visit the beautiful city of Dresden.

Uwe F.W. Behringer  
EMLC2016 Program Chair
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The 32nd European Mask and Lithography Conference, EMLC 2016, would like to express its sincere appreciation to all the sponsors and cooperating partners mentioned below for their support.

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